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MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Digital Transistors (BRT) R1 = 10 kΩ, R2 = 47 kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

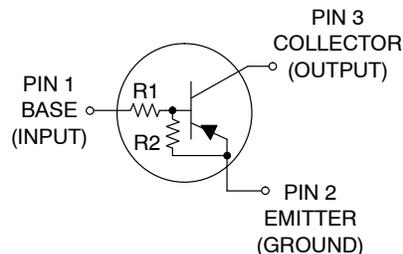
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



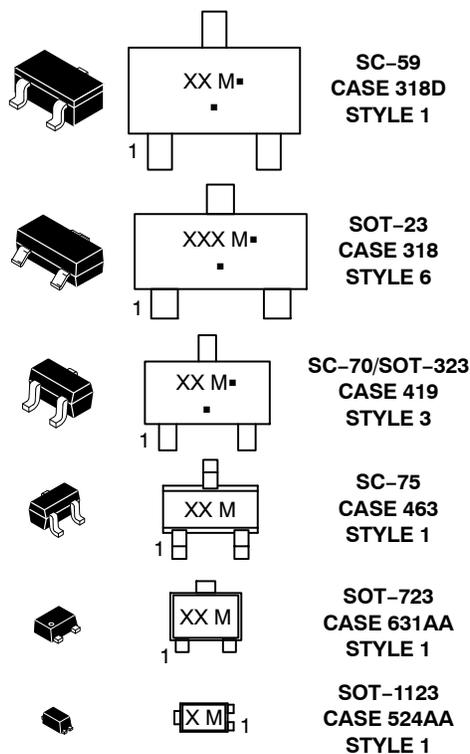
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PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

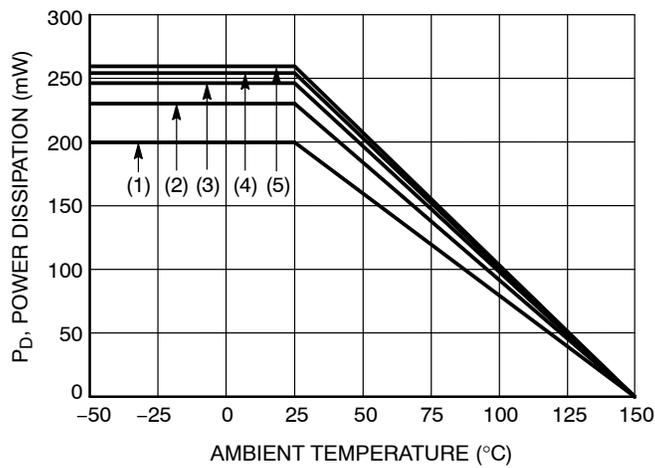
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2114T1G, SMUN2114T1G*	6D	SC-59	3,000 / Tape & Reel
MMUN2114LT1G, SMMUN2114LT1G*	A6D	SOT-23	3,000 / Tape & Reel
MMUN2114LT3G, NSVMMUN2114LT3G*	A6D	SOT-23	10,000 / Tape & Reel
MUN5114T1G, SMUN5114T1G*	6D	SC-70/SOT-323	3,000 / Tape & Reel
SMUN5114T3G	6D	SC-70/SOT-323	10,000 / Tape & Reel
DTA114YET1G, SDTA114YET1G*	6D	SC-75	3,000 / Tape & Reel
DTA114YM3T5G, NSVDTA114YM3T5G*	6D	SOT-723	8,000 / Tape & Reel
NSBA114YF3T5G	K	SOT-1123	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2114)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	230	mW
Derate above 25°C		338	$\text{mW}/^\circ\text{C}$
		1.8	
		2.7	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
		370	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264	$^\circ\text{C}/\text{W}$
		287	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SOT-23) (MMUN2114L)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	246	mW
Derate above 25°C		400	$\text{mW}/^\circ\text{C}$
		2.0	
		3.2	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
		311	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174	$^\circ\text{C}/\text{W}$
		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5114)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	202	mW
Derate above 25°C		310	$\text{mW}/^\circ\text{C}$
		1.6	
		2.5	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618	$^\circ\text{C}/\text{W}$
		403	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280	$^\circ\text{C}/\text{W}$
		332	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SC-75) (DTA114YE)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		300	$\text{mW}/^\circ\text{C}$
		1.6	
		2.4	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
		400	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SOT-723) (DTA114YM3)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	260	mW
Derate above 25°C		600	$\text{mW}/^\circ\text{C}$
		2.0	
		4.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480	$^\circ\text{C}/\text{W}$
		205	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA114YF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P_D 254 297 2.0 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$ 493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$ 193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	80	140	-	
Collector - Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	0.7	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.2\text{ V}, I_C = 1.0\text{ mA}$)	$V_{i(on)}$	1.4	0.9	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R1	7.0	10	13	k Ω
Resistor Ratio	R_1/R_2	0.17	0.21	0.25	

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS
MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3

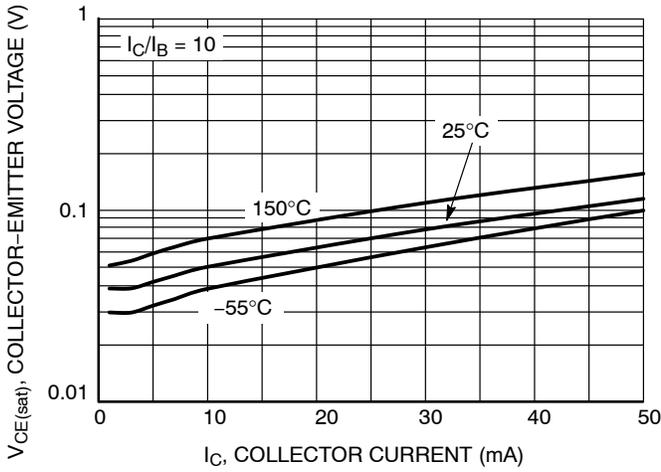


Figure 2. $V_{CE(sat)}$ vs. I_C

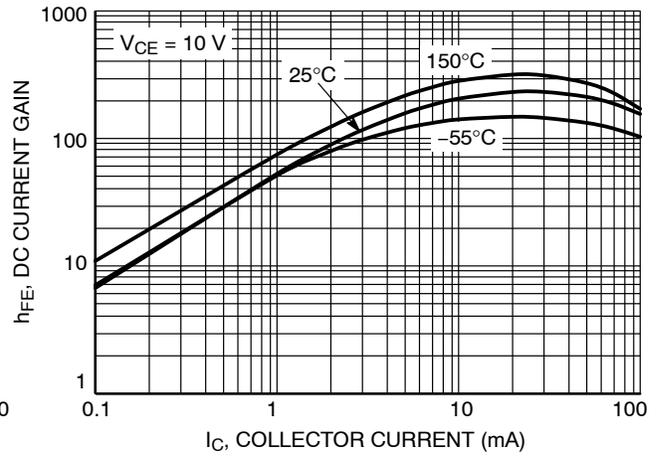


Figure 3. DC Current Gain

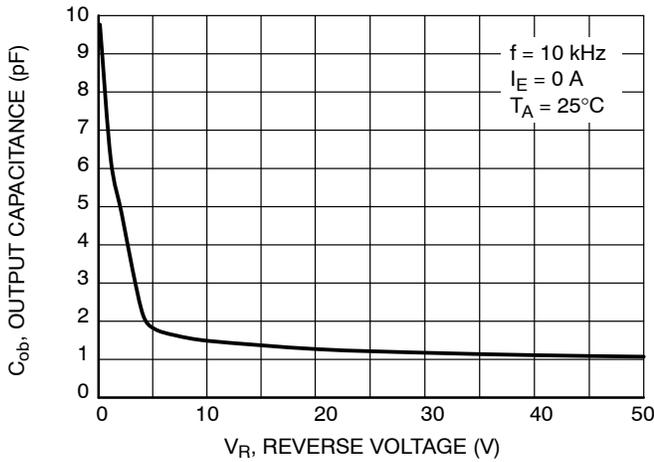


Figure 4. Output Capacitance

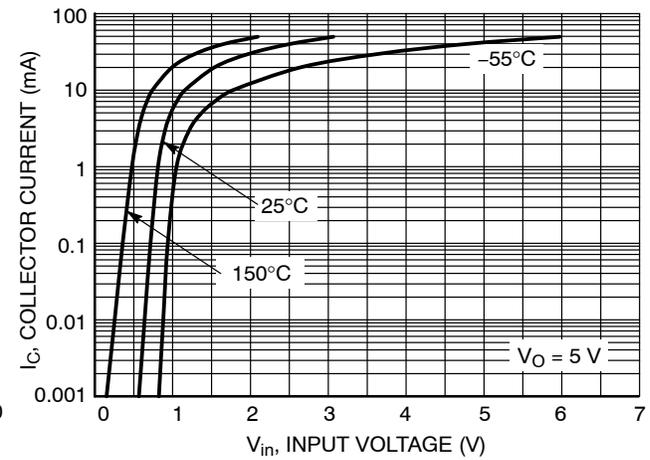


Figure 5. Output Current vs. Input Voltage

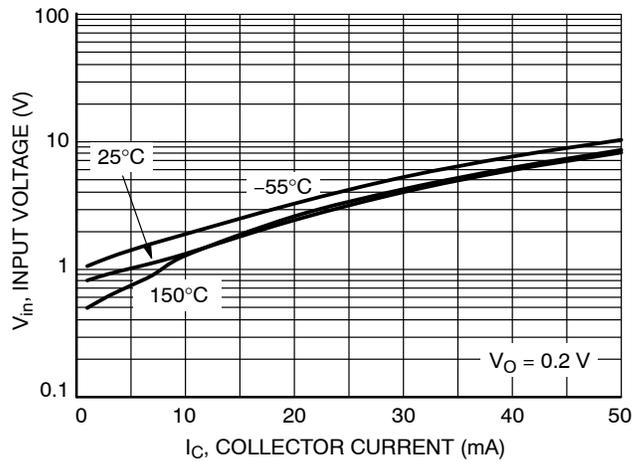


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS
NSBA114YF3

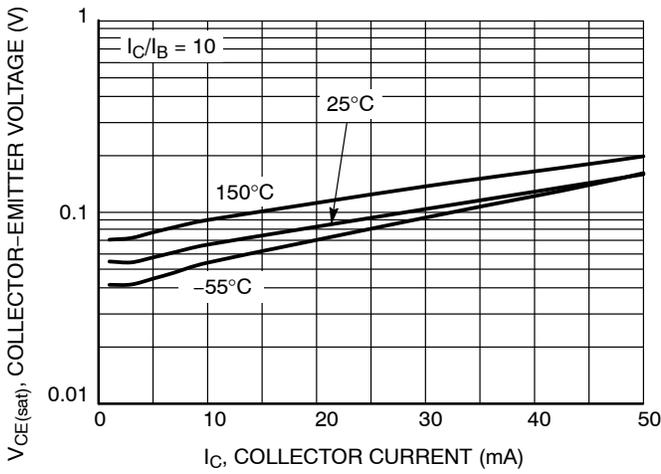


Figure 7. $V_{CE(sat)}$ vs. I_C

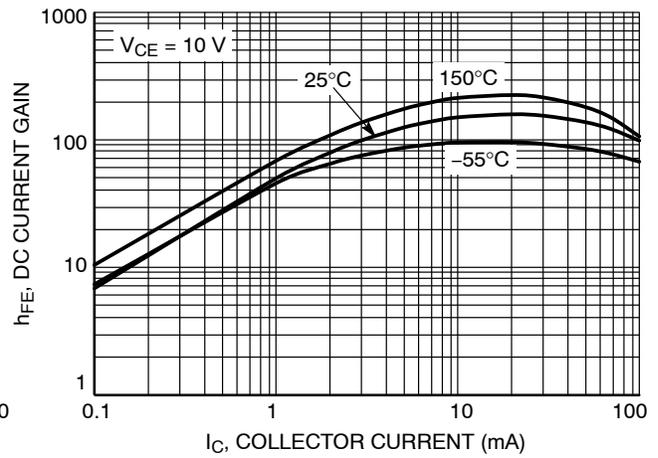


Figure 8. DC Current Gain

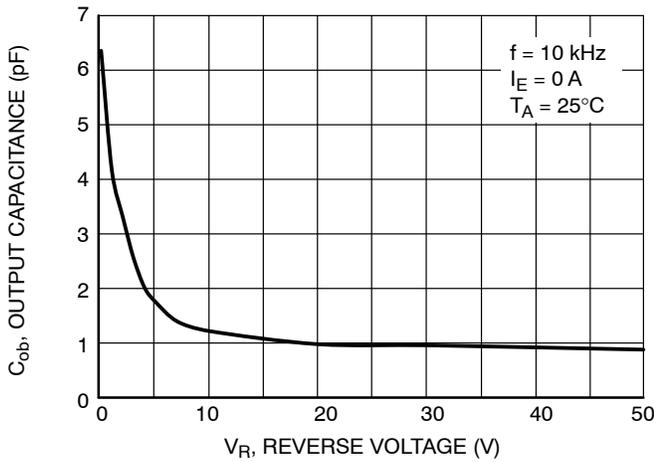


Figure 9. Output Capacitance

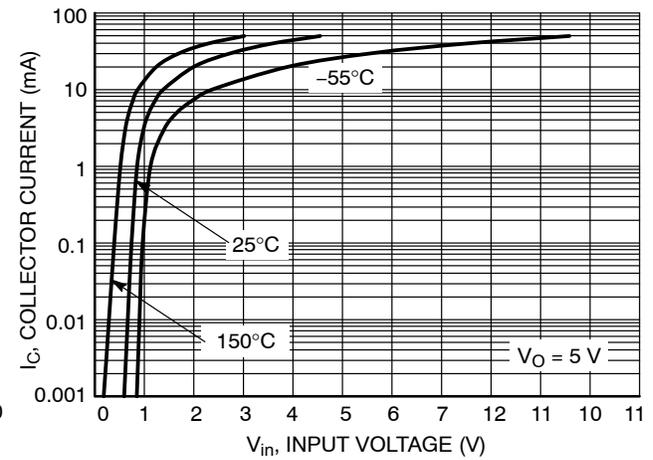


Figure 10. Output Current vs. Input Voltage

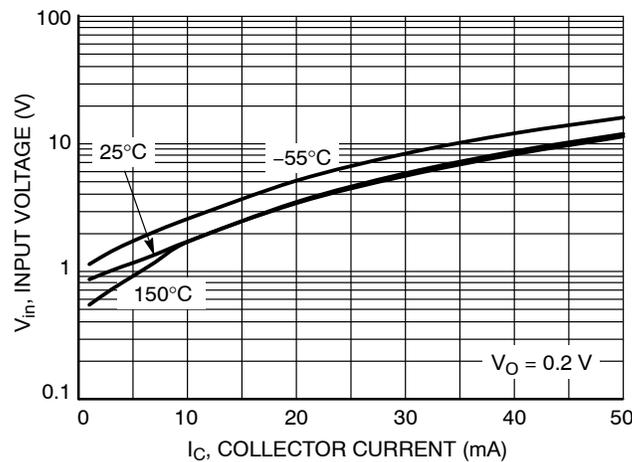
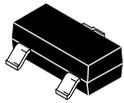


Figure 11. Input Voltage vs. Output Current

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

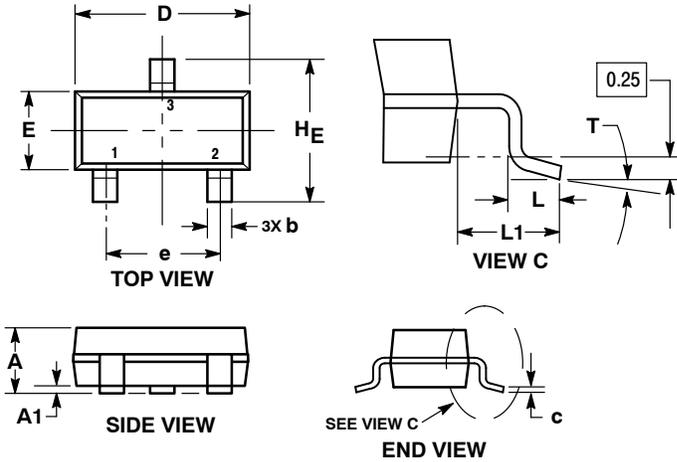
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SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

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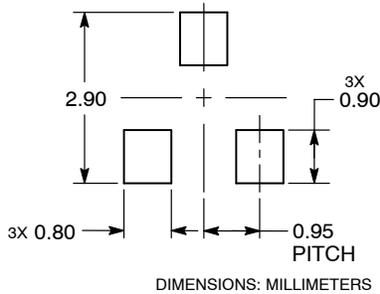


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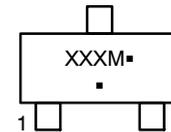
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

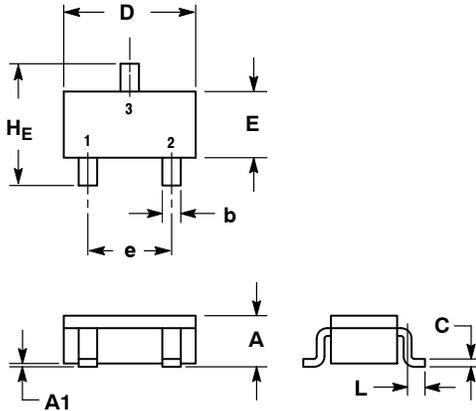
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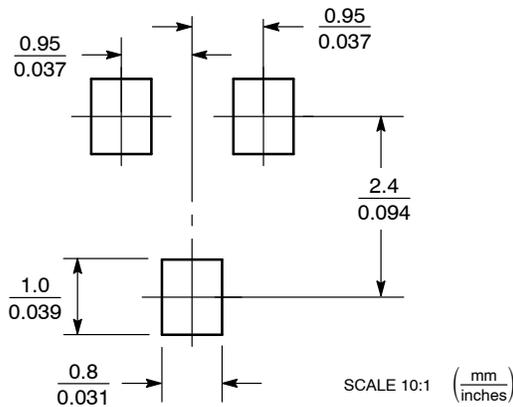
SC-59
CASE 318D-04
ISSUE H

DATE 28 JUN 2012

SCALE 2:1



SOLDERING FOOTPRINT*

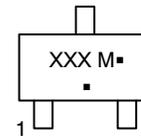


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

GENERIC MARKING DIAGRAM



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- | | | |
|---|--|--|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE |
| STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE | STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

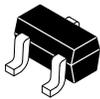
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

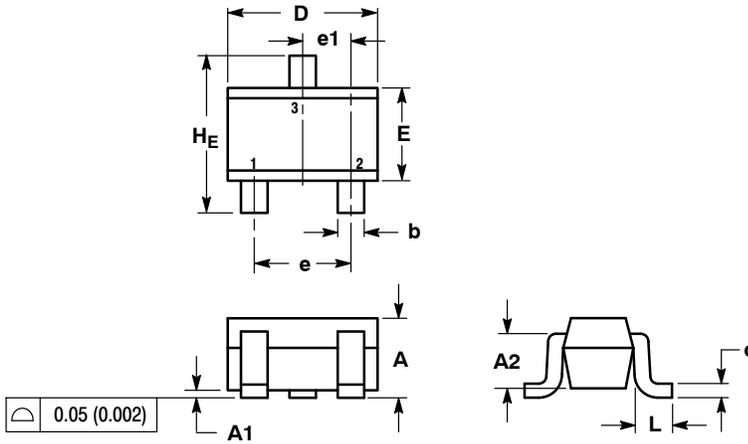
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SCALE 4:1

SC-70 (SOT-323)
CASE 419-04
ISSUE N

DATE 11 NOV 2008

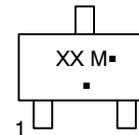


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

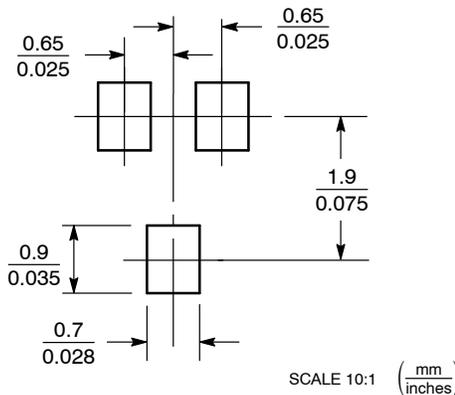
GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

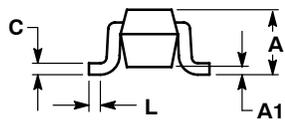
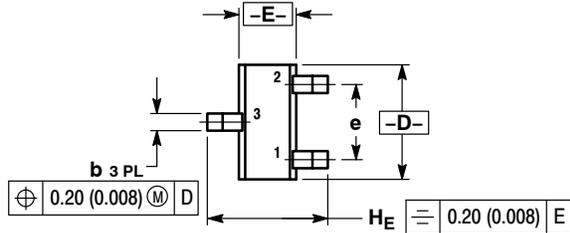
ON Semiconductor®



SC-75/SOT-416
CASE 463-01
ISSUE G

DATE 07 AUG 2015

SCALE 4:1



STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

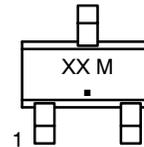
STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

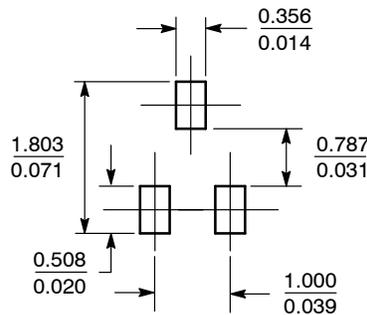
GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-75/SOT-416	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

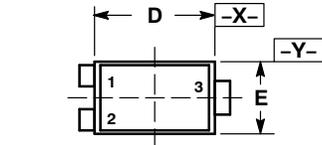
ON Semiconductor®



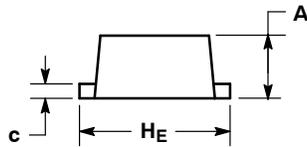
SCALE 8:1

SOT-1123
CASE 524AA
ISSUE C

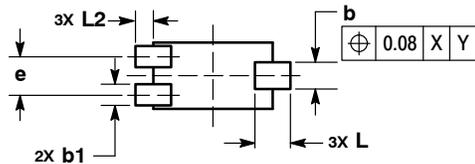
DATE 29 NOV 2011



TOP VIEW

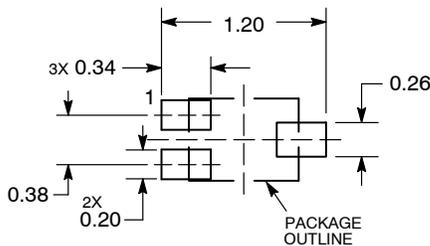


SIDE VIEW



BOTTOM VIEW

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
HE	0.95	1.05
L	0.185	REF
L2	0.05	0.15

GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

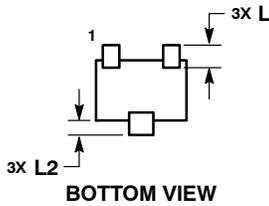
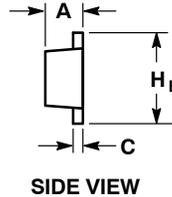
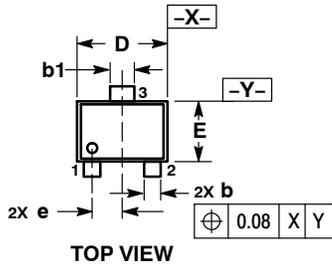
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SCALE 4:1

SOT-723
CASE 631AA-01
ISSUE D

DATE 10 AUG 2009

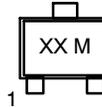


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

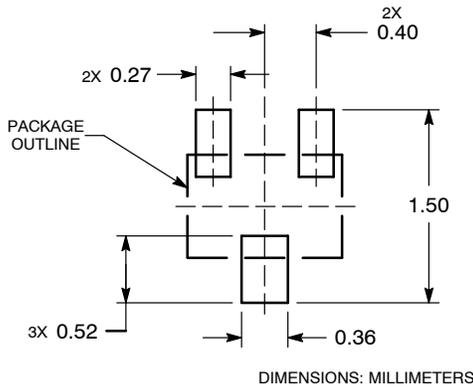
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

- | | | | | |
|---|--|--|--|--|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN |
|---|--|--|--|--|

RECOMMENDED SOLDERING FOOTPRINT*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOT-723	PAGE 1 OF 1

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